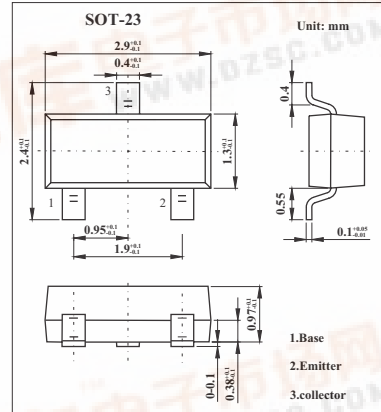


SMD Type Transistors

Silicon Pnp Epitaxial Planar Type  
2SA1245

■ Features

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■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-15	V
Collector-Emitter Voltage	V <sub>CE0</sub>	-8	V
Emitter-Base Voltage	V <sub>EB0</sub>	-2	V
Collector Current	I <sub>c</sub>	-30	mA
Base Current	I <sub>B</sub>	-15	mA
Collector Power Dissipation	P <sub>c</sub>	150	Mw
Junction Temperature	T <sub>j</sub>	125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to 125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector Cut-off Current	I <sub>cBO</sub>	V <sub>CB</sub> =-5V;I <sub>E</sub> =0			-0.1	μA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =-1V;I <sub>C</sub> =0			-0.1	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =-5V;I <sub>C</sub> =-10mA	20			
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-5V;I <sub>E</sub> =0;f=1MHz		0.75		pF
Reserve Transfer Capacitance	C <sub>re</sub>			0.60		pF
Transition Frequency	F <sub>t</sub>	V <sub>CE</sub> =-5V;I <sub>C</sub> =-10mA		4		GHz
Insertion Gain	S <sub>2e</sub>   <sup>2</sup> (1)	V <sub>CE</sub> =-5V;I <sub>C</sub> =-10mA;f=500MHz		14		dB
	S <sub>2e</sub>   <sup>2</sup> (2)	V <sub>CE</sub> =-5V;I <sub>C</sub> =-10mA;f=1GHz		9.5		dB
Noise Figure	NF(1)	V <sub>CE</sub> =-5V;I <sub>C</sub> =-3mA;f=500MHz		2.5		dB
	NF(2)	V <sub>CE</sub> =-5V;I <sub>C</sub> =-3mA;f=1GHz		3.0		dB

■ Marking

Marking	MD
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